

Silicon PNP Power Transistors

NS50A

DESCRIPTION

www.datasheet4u.com

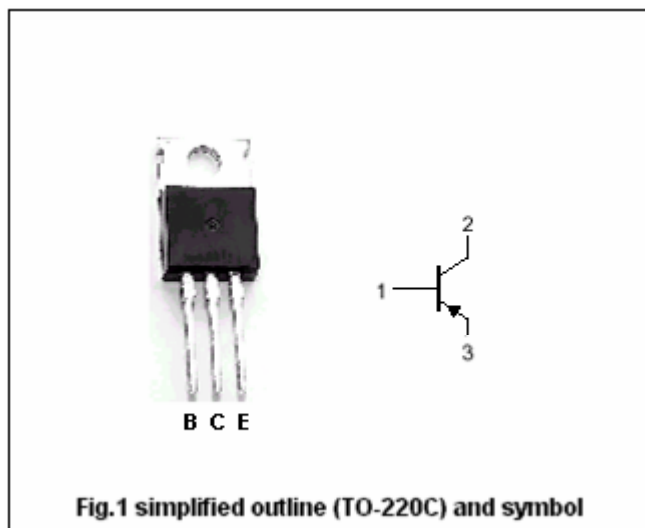
- With TO-220C package
- Complement to type NS50B

APPLICATIONS

- For medium power linear switching applications

PINNING

PIN	
1	Base
2	Collector;connected to mounting base
3	Emitter

ABSOLUTE MAXIMUM RATINGS($T_C=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current (DC)		-6	A
I_{CM}	Collector current-Pulse		-10	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	65	W
		$T_a=25^{\circ}\text{C}$	2	
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-65~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-30mA; I _B =0	-60			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-1.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-10	μA
I _{CEO}	Collector cut-off current	V _{CE} =-60V; I _B =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-10	μA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-5V	100		160	
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-10V	3			MHz

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PACKAGE OUTLINE

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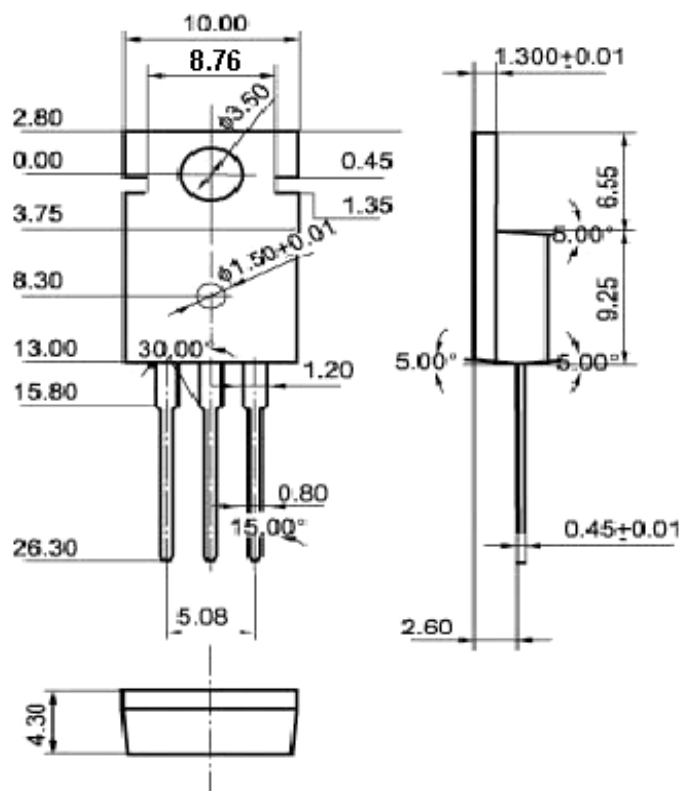


Fig.2 Outline dimensions